INC6008AC1

FOR HIGH CURRENT DRIVE APPLICATION SILICON NPN EPITAXIAL TYPE

DESCRIPTION

INC6008AC1 is a silicon NPN epitaxial type transistor. It is designed with high collector current and small $V_{\rm CE(sat)}$

FEATURE

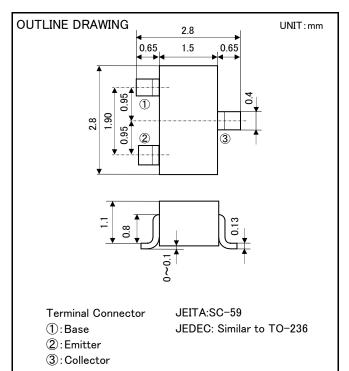
•Super mini package for easy mounting

- •High collector current($I_c=1A$)
- •Low collector saturation voltage

 $(V_{CE(sat)} < 0.7V_{max}; I_{C} = 150 \text{mA}, I_{B} = 15 \text{mA})$

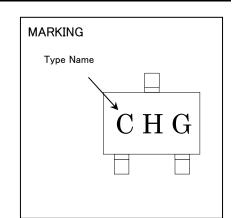
APPLICATION

Switching, Small type motor drive



MAXIMUM RATING(Ta=25°C)

SYMBOL	PARAMETER	RATING	UNIT	
V _{CBO}	Collector to Base voltage	160	V	
V _{EBO}	Emitter to Base voltage	5	V	
V _{CEO}	Collector to Emitter voltage	140	V	
Ι _c	Collector current	1	А	
Pc	Collector dissipation(Ta=25°C)	200	mW	
Tj	Junction temperature	+150	°C	
T _{stg}	Storage temperature	-55~+150	°C	



ELECTRICAL CHARACTERISTICS (Ta=25°C)

SYMBOL	PARAMETER	TEST CONDITIONS	LIMITS			UNIT
STWIDUL		TEST CONDITIONS		TYP	MAX	UNIT
V _{(BR)CBO}	C to B breakdown voltage	Ι _c =100 μ A, Ι _e =0mA	160	-	-	V
V _{(BR)EBO}	E to B breakdown voltage	I _E =100 μ A, I _C =0mA	5	-	Ι	V
V _{(BR)CEO}	C to E breakdown voltage	I _c =10mA, R _{BE} =∞	140	_	-	V
I _{CBO}	Collector cut off current	V _{CB} =140V, I _E =0mA	-	-	100	nA
I _{EBO}	Emitter cut off current	V _{EB} =4V, I _c =0mA	-	-	100	nA
h _{FE}	DC forward current gain	V _{ce} =10V, I _c =150mA	100	-	300	-
V _{CE(sat)}	C to E saturation voltage	I _c =150mA, I _B =15mA	-	-	0.7	V
$V_{BE(sat)}$	B to E saturation voltage	I _c =150mA, I _B =15mA	-	-	1.1	V
f _T	Gain bandwidth product	V_{ce} =10V, I _e =-50mA, f=100MHz	100	-	Ι	MHz
Cob	Collector output capacitance	V _{CB} =10V, f=1MHz	-	-	15	pF

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COLLECTOR TO BASE VOLTAGE VCB(V)

DC FORWARD CURRENT GAIN COMMON EMITTER TRANSFER VS. COLLECTOR CURRENT 1000 1000 VCE=10V VCE=10V Ta=85°C DC FORWARD CURRENT GAIN hFE (-) COLLECTOR CURRENT IC(mA) 100 Ta=85°C 100 \setminus 10 Ta=25°C Ta=−40°C Ta=25°C 1 10 Ta=-40°C 0.1 1 0.01 1 100 1000 10 0 0.2 0.4 0.6 0.8 1.2 1 COLLECTOR CURRENT IC (mA) BASE TO EMITTER VOLTAGE VBE(V) COLLECTOR TO EMITTERSATURATION BASE TO EMITTERSATURATION VOLTAGE VOLTAGE VS. COLLECTOR CURRENT VS. COLLECTOR COLLECTOR TO EMITTERSATURATION VOLTAGE 1 10 IC/IB=10/1 BASE TO EMITTERSATURATION VOLTAGE IC/IB=10/1 85°C Ta=25°C 0.1 VCE(sat) (V) -40°C Ta= VBE(sat) (V) Ta=25°C 1 <u>Ta=-40°</u>C 0.01 Ta=85°C 0.001 0.1 10 100 1000 1000 1 10 100 COLLECTOR CURRENT IC (mA) COLLECTOR CURRENT IC (mA) GAIN BAND WIDTH PRODUCT COLLECTOR OUTPUT CAPACITANCE VS. EMITTER CURRENT VS. COLLECTOR TO BAS 1000 100 COLLECTOR OUTPUT CAPACITANCE Cob(pF) IE=0 GAIN BAND WIDTH PRODUCT FT(MHz) VCF=10V f=1MHz 100 10 10 1 1 0.1 10 100 1 0.1 10 100 1

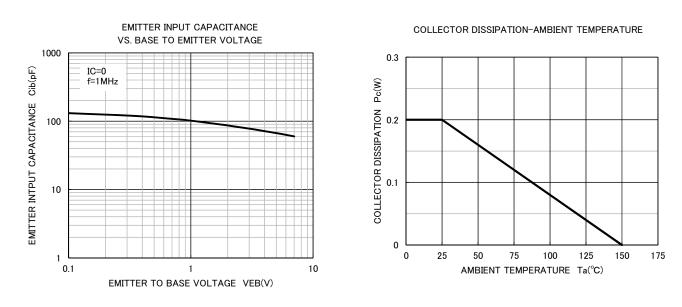
TYPICAL CHARACTERISTICS (Ta=25°C)

ISAHAYA ELECTRONICS CORPORATION

EMITTER CURRENT IE(mA)

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FOR HIGH CURRENT DRIVE APPLICATION SILICON NPN EPITAXIAL TYPE



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